

## **isc Silicon PNP Power Transistors**

# TIP32B

#### **DESCRIPTION**

- · Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)} = -1.2V(Max.)@I_{C} = -3.0A$
- · Collector-Emitter Sustaining Voltage-
  - $: V_{CEO(SUS)} = -80V(Min)$
- Complement to Type TIP31B
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



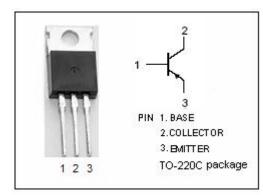
 Designed for use in general purpose amplifier and switching applications.

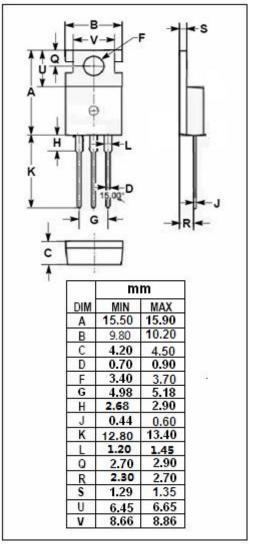
### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-base Voltage	-80	V	
V <sub>CEO</sub>	Collector-emitter Voltage	-80	٧	
V <sub>EBO</sub>	Emitter-base Voltage	-5	V	
Ic	Collector Current-Continuous	-3	Α	
I <sub>CM</sub>	Collector Current-Pulse	-5	Α	
I <sub>B</sub>	Base Current	-1	Α	
Pc	Collector Power Dissipation $T_C$ =25 $^{\circ}$ C	40	W	
	Collector Power Dissipation $T_a$ =25 $^{\circ}$ C	2		
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Ttemperature Range	-65~150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	3.125	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient	62.5	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-80		V
VCE(sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.375A		-1.2	V
VBE(on)	Base-Emitter On Voltage	I <sub>C</sub> = -3A ; V <sub>CE</sub> = -4V		-1.8	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = -80V; V <sub>EB</sub> = 0		-0.2	mA
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -60V; I <sub>B</sub> = 0		-0.3	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -4V	25		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -4V	10	50	
f⊤	Current-Gain—Bandwidth Product	Ic= -0.5A ; VcE= -10V	3		MHz

#### **NOTICE:**

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